

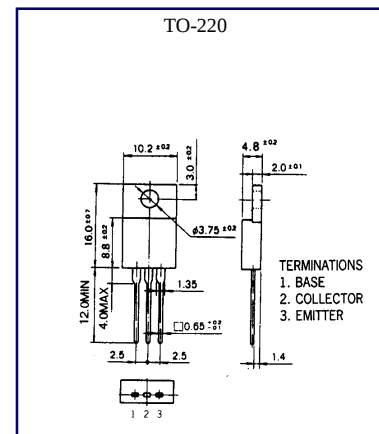


TIP41 SERIRES (TIP41/41A/41B/41C)

NPN EPITAXIAL SILICON TRANSISTOR

MEDIUM POWER LINEAR SWITCHING APPLICATIONS

●Complementary to TIP42/42A/42B/42C



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage :TIP41	V _{CB0}	40	V
:TIP41A		60	V
:TIP41B		80	V
:TIP41C		100	V
Collector-Emitter Voltage :TIP41	V _{CE0}	40	V
:TIP41A		60	V
:TIP41B		80	V
:TIP41C		100	V
Emitter-Base voltage	V _{EB0}	5	V
Collector Current (DC)	I _C	6	A
Collector Current (Pulse)	I _C	10	A
Base Current (DC)	I _B	2	A
Collector Dissipation (T _c =25°C)	P _C	65	W
Junction Temperature	T _j	150	
Storage Temperature	T _{stg}	-50~150	

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Emitter Sustaining Voltage :TIP41	BV _{CEO(SUS)}	I _C =30mA, I _B =0	40			V
:TIP41A			600			V
:TIP41B			80			V
:TIP41C			100			V
Collector Cutoff Current :TIP41/41A	I _{CEO}	V _{CE} = 30V , I _B =0			0.7	mA
:TIP41B/41C		V _{CE} = 60V , I _B =0			0.7	mA
Collector Cutoff Current :TIP41	I _{CES}	V _{CE} = 40V , V _{EB} =			400	μA
:TIP41A		0			400	μA
:TIP41B		V _{CE} = 60V , V _{EB} =			400	μA
:TIP41C		0			400	μA
Emitter Cutoff Current	I _{EBO}	V _{CE} = 80V , V _{EB} =			1	mA
DC Current Gain	h _{FE}	0	30			
		V _{CE} = 100V , V _{EB} =	15		75	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	0			1.5	V
Base- Emitter On Voltage	V _{BE(on)}	V _{EB} = 5V , I _C =0			2.0	V
Current Gain Bandwith Product	f _T	V _{CE} = 4V , I _C =0.3A	3.0			MHZ
		V _{CE} = 4V , I _C =3A				
		I _C =6A , I _B =600mA				
		V _{CE} = 4V , I _C =6A				
		V _{CE} = 10V ,				
		I _C =500mA				
		f=1MHZ				